

# LNA2606L

## GaAlAs on GaAs Infrared Light Emitting Diode

For optical control systems

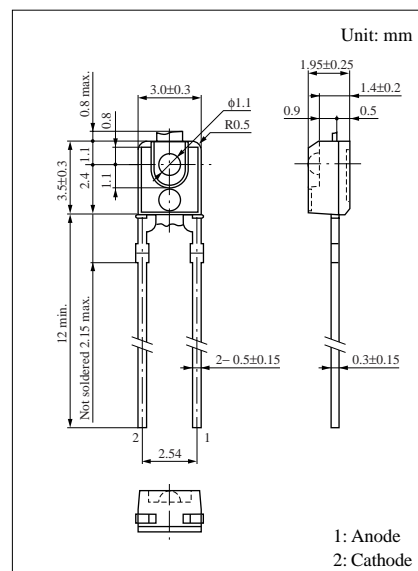
### ■ Features

- High-power output, high-efficiency:  $P_O = 9 \text{ mW min.}$
- Emitted light spectrum suited for silicon photodetectors
- Ultra-miniature, thin side-view type package
- Long lifetime, high reliability

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Power dissipation	$P_D$	80	mW
Forward current (DC)	$I_F$	50	mA
Pulse forward current *	$I_{FP}$	1	A
Reverse voltage (DC)	$V_R$	3	V
Operating ambient temperature	$T_{opr}$	-25 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +100	$^\circ\text{C}$

Note) \*:  $f = 100 \text{ Hz}$ , Duty Cycle = 0.1%



### ■ Electro-Optical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	$P_O$	$I_F = 50 \text{ mA}$	9		19	mW
Peak emission wavelength	$\lambda_p$	$I_F = 50 \text{ mA}$		940		nm
Spectral half band width	$\Delta\lambda$	$I_F = 50 \text{ mA}$		50		nm
Forward voltage (DC)	$V_F$	$I_F = 50 \text{ mA}$		1.3	1.6	V
Reverse current (DC)	$I_R$	$V_R = 3 \text{ V}$			10	$\mu\text{A}$
Capacitance between pins	$C_t$	$V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$		35		pF
Half-power angle	$\theta$	The angle in which radiant intensity is 50%		20		$^\circ$